

Features

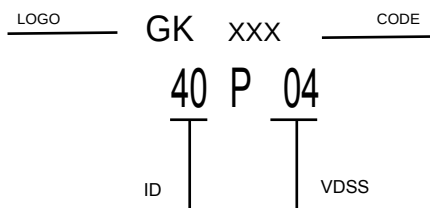
The AOD4185 is the high cell density trench P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The AOD4185 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Applications

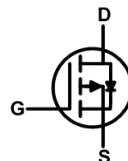
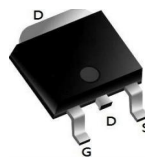
100% EAS Guaranteed
Green Device Available
Super Low Gate Charge
Excellent CdV/dt effect decline
Advanced high cell density Trench technology

V_{DS} -40 V
 I_D -40 A
 $R_{DS(ON)}$ 10.5mΩ



TO-252

Equivalent Circuit



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	-40	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	$T_C=25^\circ\text{C}$	I_D	-40	A
	$T_C=100^\circ\text{C}$		-31	
Pulsed Drain Current ¹		I_{DM}	-200	A
Single Pulse Avalanche Energy ²		EAS	80	mJ
Total Power Dissipation	$T_C=25^\circ\text{C}$	P_D	55	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ³	$R_{\theta JA}$	61	°C/W
Thermal Resistance from Junction-to-Case	$R_{\theta JC}$	2.27	°C/W

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-40	-	-	V
Gate-body Leakage current		I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	± 100	nA
Zero Gate Voltage Drain Current	$T_J=25^{\circ}C$	I_{DSS}	$V_{DS} = -40V, V_{GS} = 0V$	-	-	1	μA
	$T_J=100^{\circ}C$			-	-	5	
Gate-Threshold Voltage		$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.0	-1.6	-2.5	V
Drain-Source On-Resistance ⁴		$R_{DS(on)}$	$V_{GS} = -10V, I_D = -16A$	-	10.5	13	mΩ
			$V_{GS} = -4.5V, I_D = -12A$	-	14.2	20	
Forward Transconductance ⁴		g_{fs}	$V_{DS} = -10V, I_D = -16A$	-	44	-	S
Dynamic Characteristics ⁵							
Input Capacitance		C_{iss}	$V_{DS} = -20V, V_{GS} = 0V, f = 1MHz$	-	3050	-	pF
Output Capacitance		C_{oss}		-	282	-	
Reverse Transfer Capacitance		C_{rss}		-	230	-	
Gate Resistance		R_g	$f = 1MHz$	-	9	-	Ω
Switching Characteristics ⁵							
Total Gate Charge		Q_g	$V_{GS} = -10V, V_{DS} = -20V, I_D = -16A$	-	28	-	nC
Gate-Source Charge		Q_{gs}		-	8	-	
Gate-Drain Charge		Q_{gd}		-	8.5	-	
Turn-on Delay Time		$t_{d(on)}$	$V_{GS} = -10V, V_{DD} = -15V, R_G = 3\Omega, I_D = -16A$	-	38	-	ns
Rise Time		t_r		-	31	-	
Turn-off Delay Time		$t_{d(off)}$		-	90	-	
Fall Time		t_f		-	9.2	-	
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ⁴		V_{SD}	$I_S = -1A, V_{GS} = 0V$	-	-	-1.2	V
Continuous Source Current	$T_C=25^{\circ}C$	I_S	-	-	-	-50	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^{\circ}\text{C}$.
2. The EAS data shows Max. rating . The test condition is $V_{DD} = -25V, V_{GS} = -10V, L=0.1\text{mH}, I_{AS} = -40A$.
3. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
5. This value is guaranteed by design hence it is not included in the production test..

RATING AND CHARACTERISTIC CURVES

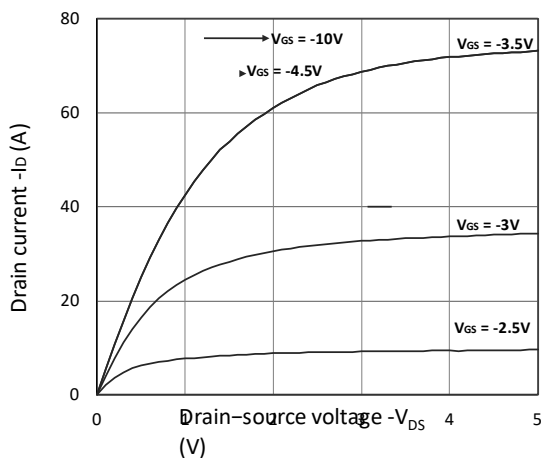


Figure 1. Output Characteristics

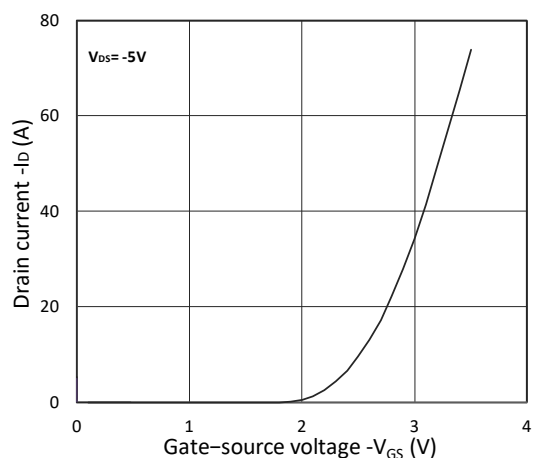


Figure 2. Transfer Characteristics

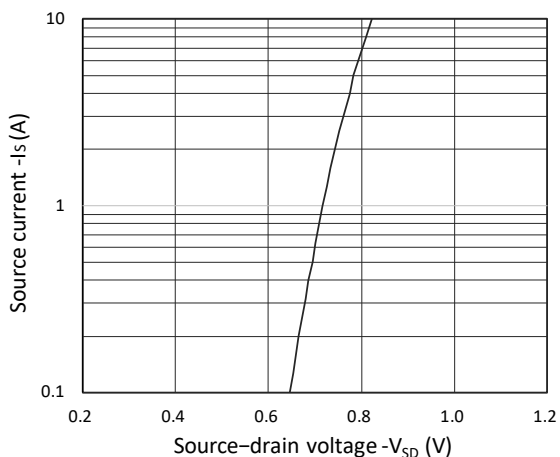


Figure 3. Forward Characteristics of Reverse

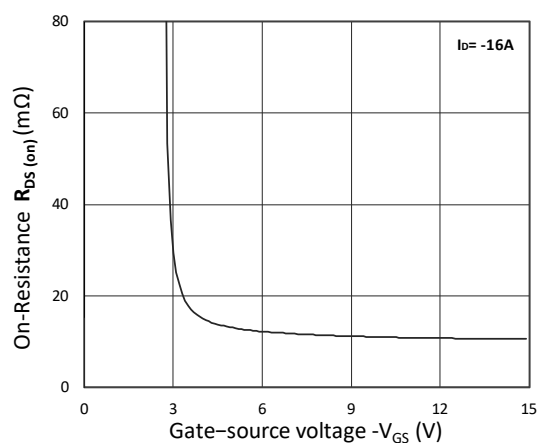


Figure 4. $R_{DS(on)}$ vs. V_{GS}

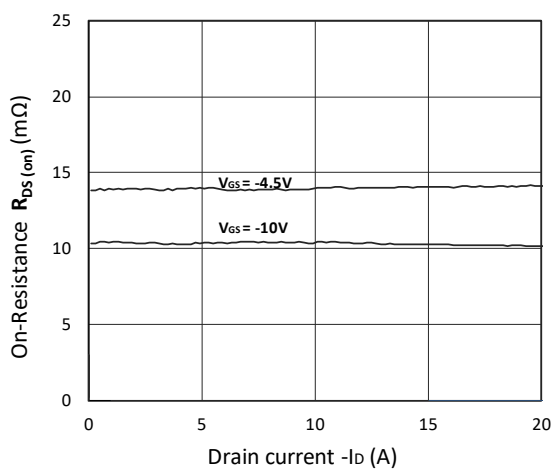


Figure 5. $R_{DS(on)}$ vs. I_D

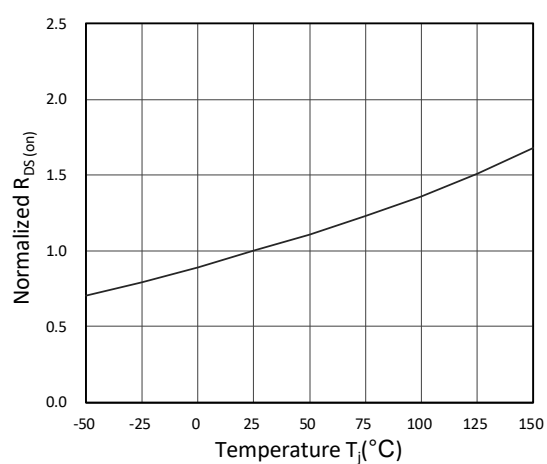


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

RATING AND CHARACTERISTIC CURVES

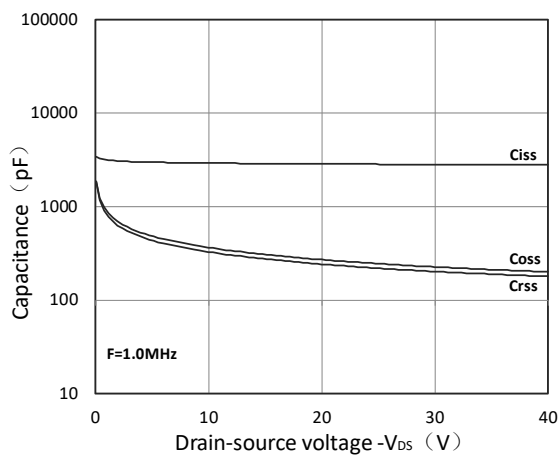


Figure 7. Capacitance Characteristics

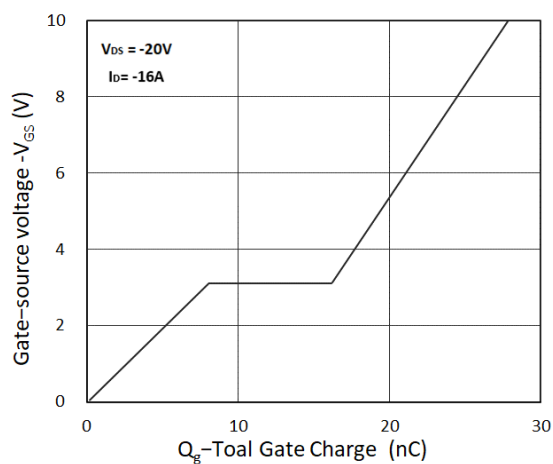


Figure 8. Gate Charge Characteristics

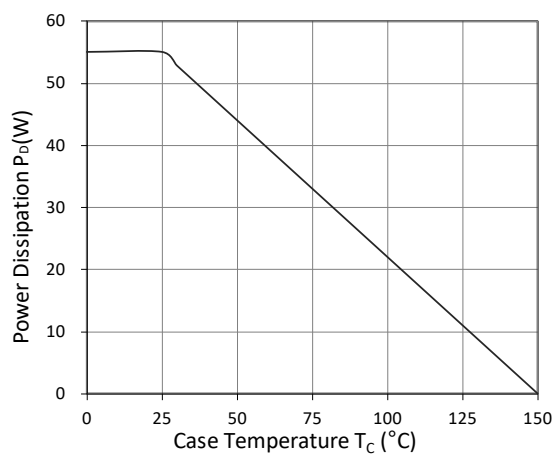


Figure 9. Power Dissipation

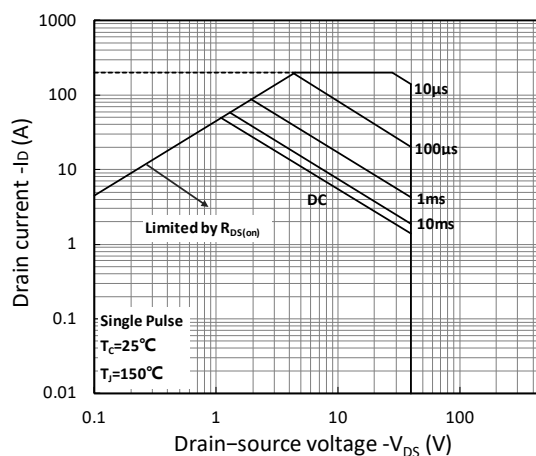


Figure 10. Safe Operating Area

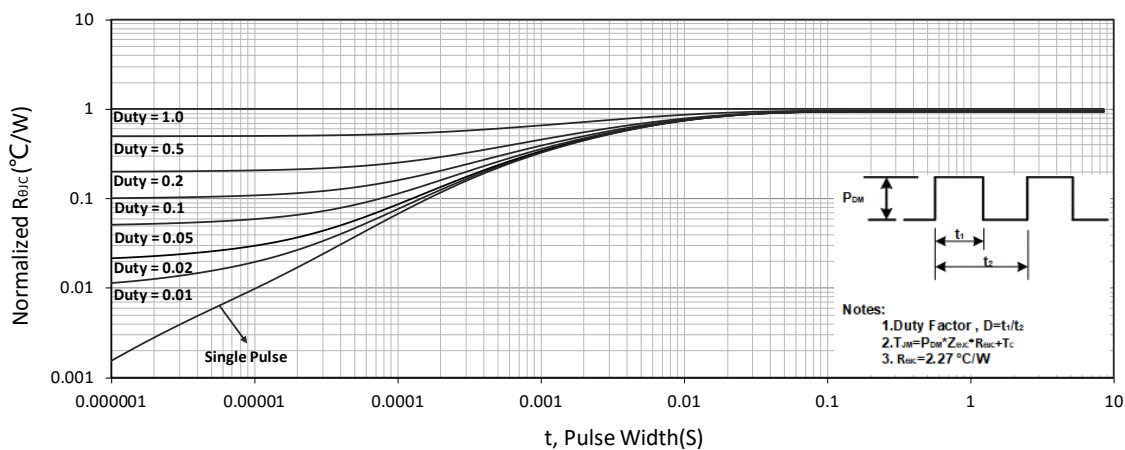


Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

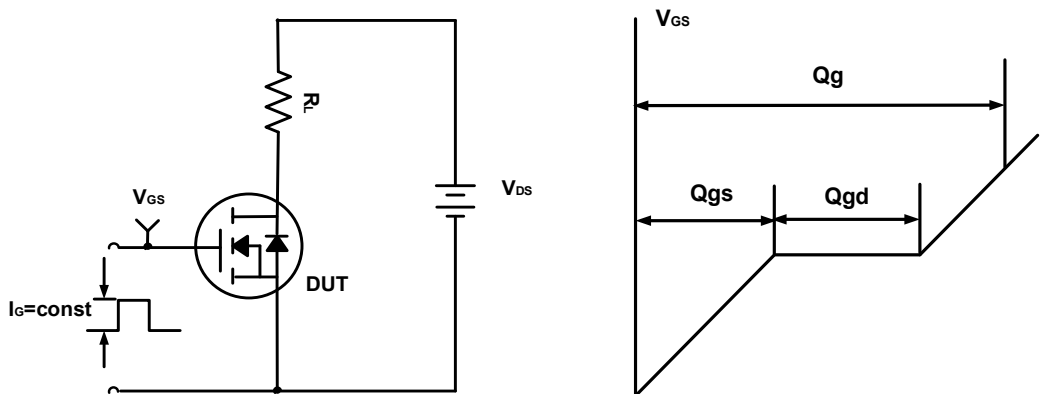


Figure A. Gate Charge Test Circuit & Waveforms

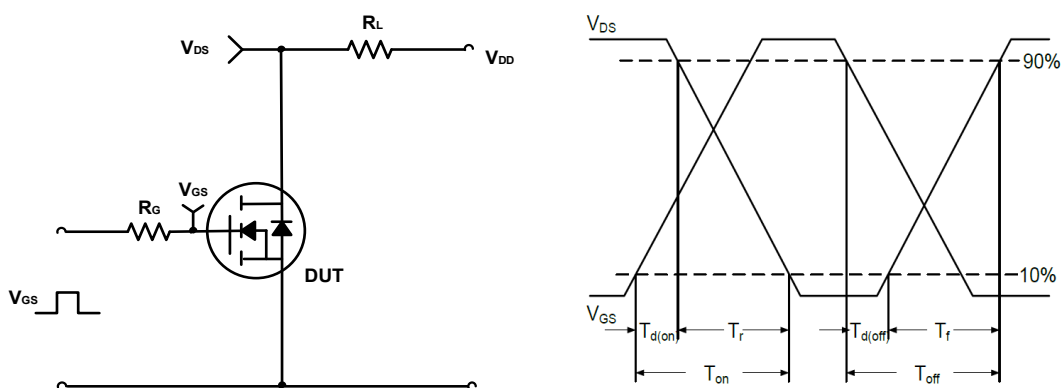


Figure B. Switching Test Circuit & Waveforms

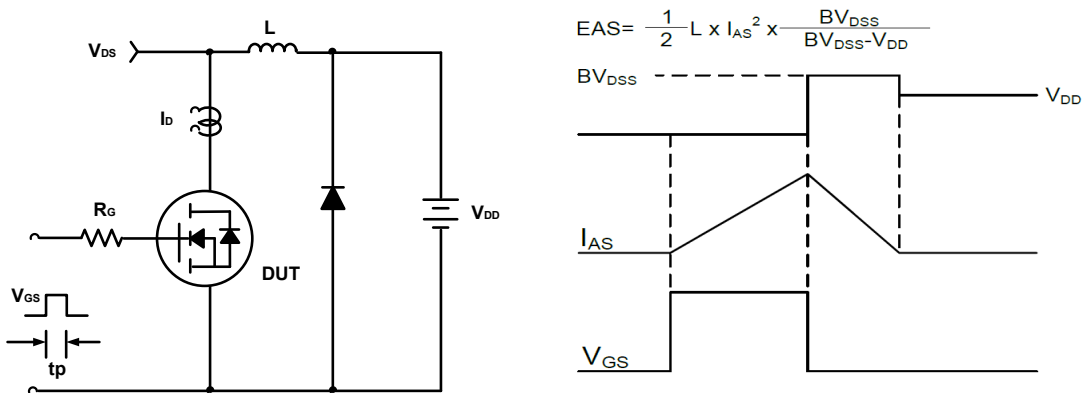
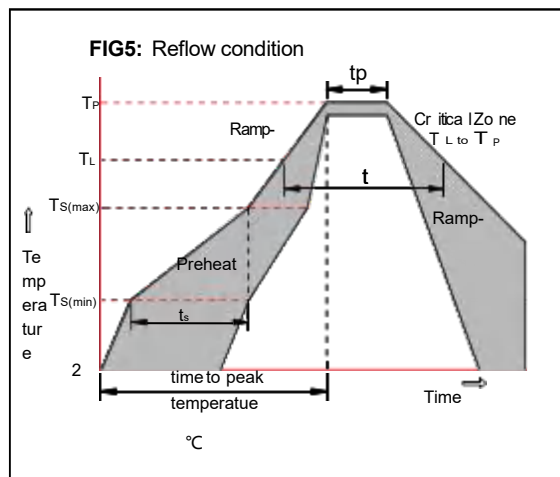


Figure C. Unclamped Inductive Switching Circuit & Waveforms

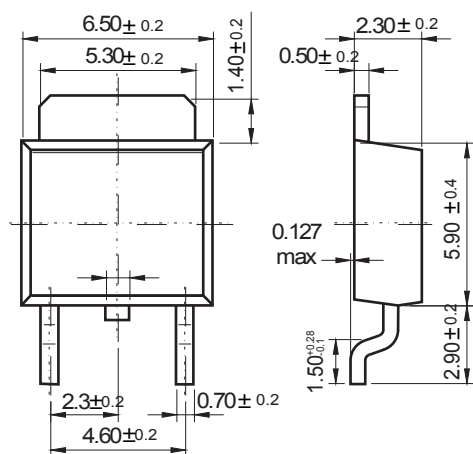
Soldering parameters

Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_P)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260°C

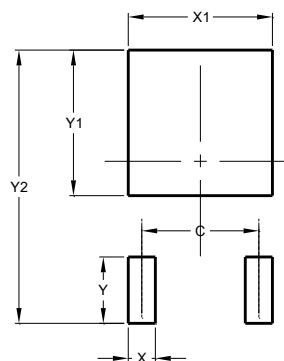


Package Dimensions & Suggested Pad Layout

TO-252



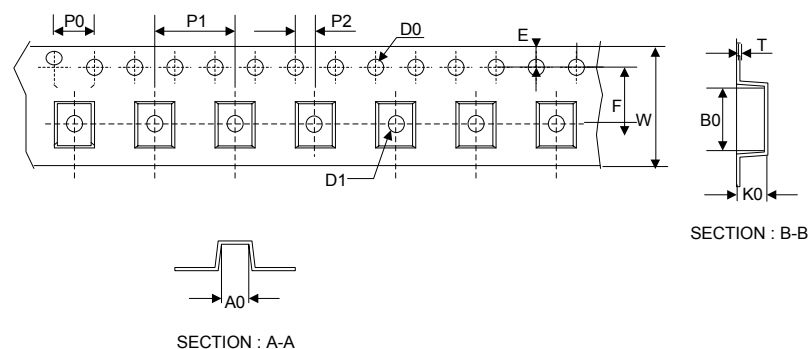
Dimensions in inches and (millimeters)



Dimensions	Value (in mm)
C	4.55
X	1.50
X1	5.80
Y	2.70
Y1	6.00
Y2	10.90

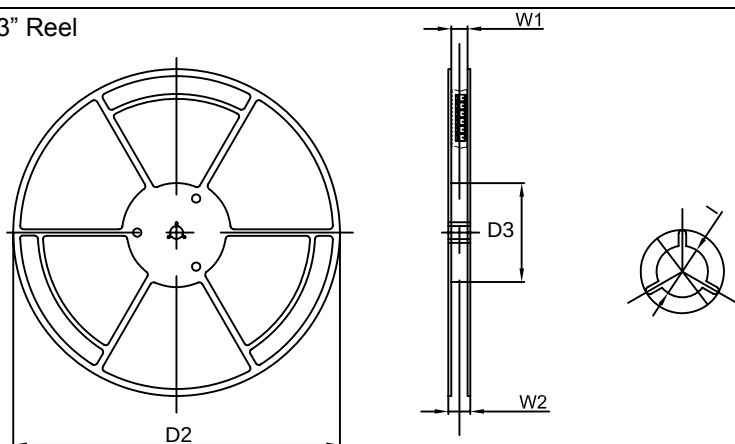
Tape & rell specification

Tape



Symbol	Dimension (mm)
P0	4.00±0.20
P1	8.00±0.20
P2	2.00±0.20
D0	1.55±0.15
D1	1.55±0.20
E	1.75±0.20
F	7.50±0.20
W	16.00±0.20
A0	7.10±0.20
B0	10.50±0.20
K0	2.70±0.20
T	0.30±0.10
D2	330.0±5.0
D3	100.0±4.0
W1	20.0±5.0
W2	25.0±5.0
I	13.0±2.0

13" Reel



Quantity: 2500PCS